



Indium-Gallium-Zinc Oxide (IGZO) Sputtering Target

❖ Product Introduction

Indium Gallium Zinc Oxide (IGZO) sputtering target is a high-purity oxide ceramic target material composed of Indium oxide (In_2O_3), Gallium oxide (Ga_2O_3), and Zinc oxide (ZnO). It features excellent composition uniformity, high density, stable sputtering performance, and good thin-film forming capability. IGZO targets exhibit excellent electrical properties, optical transparency, and chemical stability, making them widely used for oxide semiconductor thin film deposition and advanced electronic applications.

❖ Product Characteristics

1. High purity, uniform composition, and excellent material consistency.
2. High density, stable sputtering performance, and low particle generation.
3. Excellent electrical properties and thin-film deposition performance.
4. Good thermal stability, chemical stability, and compatibility with oxide semiconductor applications.

❖ Product Specifications

Product ID	Formula	Purity	Size
49083108300800ST001	$\text{In}_2\text{O}_3\text{-Ga}_2\text{O}_3\text{-ZnO}$	99.99%	Ø 50.8 mmx3.175 mm
49083108300800ST002	$\text{In}_2\text{O}_3\text{-Ga}_2\text{O}_3\text{-ZnO}$	99.99%	Ø 50.8 mmx6.35 mm
49083108300800ST003	$\text{In}_2\text{O}_3\text{-Ga}_2\text{O}_3\text{-ZnO}$	99.99%	Ø 76.2 mmx3.175 mm
49083108300800ST004	$\text{In}_2\text{O}_3\text{-Ga}_2\text{O}_3\text{-ZnO}$	99.99%	Ø 101.6 mmx4 mm
49083108300800ST005	$\text{In}_2\text{O}_3\text{-Ga}_2\text{O}_3\text{-ZnO}$	99.99%	Ø 101.6 mmx6.35 mm
49083108300800ST006	$\text{In}_2\text{O}_3\text{-Ga}_2\text{O}_3\text{-ZnO}$	99.99%	Ø 152.4 mmx3.175 mm
49083108300800ST007	$\text{In}_2\text{O}_3\text{-Ga}_2\text{O}_3\text{-ZnO}$	99.99%	Ø 152.4 mmx6.35 mm
49083108300800ST008	$\text{In}_2\text{O}_3\text{-Ga}_2\text{O}_3\text{-ZnO}$	99.99%	Ø 203.2 mmx6.35 mm
49083108300800STC01	Custom IGZO ratio	Customized	Customized

Total Purity	Impurity Elements (ppm)					
	Co	Cu	Mn	Cr	Ni	Na
99.99%	≤20	≤20	≤10	≤10	≤10	≤10

❖ Typical Applications

IGZO sputtering targets are widely used in oxide semiconductor thin-film deposition for thin-film transistor (TFT) displays, flat-panel display applications, transparent electronic devices, oxide semiconductor research and advanced PVD thin-film applications.

❖ Packaging

Outer packaging: wooden case or carton.

Inner packaging: vacuum-sealed bag with protective materials.

Packing specification: 1 Pcs/bag

Customized packaging is available upon request.

❖ Storage

During transportation and storage, avoid moisture, contamination and direct sunlight. Keep away from fire sources and corrosive substances. Use the bag as soon as it is opened. The shelf life is no more than 24 months from the production date.

❖ Custom specifications are available, including

- Customized In/Ga/Zn composition ratio
- Different target dimensions and shapes
- Higher density requirements
- Customized bonding options
- Special surface finishing requirements

❖ Cautions

This product is harmful if swallowed or inhaled, and may cause skin and eye irritation. Inhalation may irritate the respiratory tract; avoid inhalation. We recommend that customers inform us of their intended use before purchasing to ensure proper product use.

Disclaimer

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